

IN THE CLAIMS:

Please cancel claims 12 and 22, without prejudice, and substitute amended claims 1-11, 13-21 and 23-25 as follows:

1. (Amended) A semiconductor device comprising:

a' a semiconductor substrate including a circuit element-forming region in which an integrated circuit is formed, and a plurality of connection pads;

5 an organic insulating film formed on said circuit element-forming region;

a plurality of columnar electrodes which are provided for connection to external terminals, and which are each electrically connected to at least one of said plurality of connection pads;

10 at least one thin film passive element including at least one conductive layer formed on said insulating film; and

a sealing film which is provided between the columnar electrodes and covers the at least one thin film passive element, and from which an upper edge surface of each of the columnar electrodes is exposed.

15 2. (Amended) The semiconductor device according to claim 1, wherein said thin film passive element comprises at least one capacitance element.

3. (Amended) The semiconductor device according to claim 2,  
wherein:

said capacitance element includes two conductive layers and  
a dielectric material layer,

said two conductive layers are stacked one upon the other on  
said insulating film, and

said dielectric material layer is interposed between the  
conductive layers.

4. (Amended) The semiconductor device according to claim 2,  
wherein:

said at least one conductive layer of said capacitance  
element includes at least two portions formed in one layer on  
said insulating film, and

a dielectric material layer is formed in a clearance between  
the at least two portions.

5. (Amended) The semiconductor device according to claim 2,  
wherein:

said at least one conductive layer of said capacitance  
element includes at least two portions formed in one layer on  
said insulating film,

said columnar electrodes are formed as plate-like electrodes  
respectively positioned on the at least two portions, and

a dielectric material layer is formed in a clearance between  
surfaces of the plate-like electrodes.

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6. (Amended) The semiconductor device according to claim 1,  
wherein said thin film passive element comprises at least one  
inductance element.

7. (Amended) The semiconductor device according to claim 6,  
wherein:

said inductance element includes one conductive layer having  
one of an angular eddy shape, a rectangular wave shape, and a  
5 loop shape,

said connection pads include at least one first connection  
pad that is not electrically connected to any of said columnar  
electrodes, and at least one second connection pad electrically  
connected to at least one of said columnar electrodes, and

10 said inductance element includes at least two terminals, at  
least one of which is connected to at least one of said first  
connection pad and said second connection pad.

8. (Amended) The semiconductor device according to claim 7,  
wherein said inductance element further comprises a magnetic film  
formed on said one conductive layer.

9. (Amended) The semiconductor device according to claim 1,  
wherein said thin film passive element includes at least two  
terminals, at least one of which is electrically connected to one  
of said columnar electrodes.

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a,  
10. (Amended) The semiconductor device according to claim 1, wherein said thin film passive element includes at least two terminals, at least one of which is electrically connected to one of said connection pads.

11. (Amended) The semiconductor device according to claim 1, wherein said thin film passive element includes at least two terminals, each of which is electrically connected to at least one of said connection pads and said columnar electrodes.

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13. (Amended) The semiconductor device according to claim 1, wherein said at least one thin film passive comprises a plurality of thin film passive elements.

14. (Amended) A method of manufacturing a semiconductor device comprising:

preparing a semiconductor wafer substrate including a plurality of chip forming regions each having a circuit  
5 element-forming region in which an integrated circuit is formed, and a plurality of connection pads;

forming an organic insulating film on the circuit element-forming region of each of said chip forming regions;

forming a plurality of columnar electrodes which are  
10 provided for connection to an external terminals, and which are

each electrically connected to at least one of said plurality of connection pads;

forming a plurality of thin film passive elements each including at least one conductive layer on said insulating film;

14 forming a sealing film on the semiconductor wafer substrate between the columnar electrodes and covering the thin film passive elements and the columnar electrodes;

exposing an upper edge surface of each of the columnar electrodes from the sealing film; and

20 dividing said semiconductor wafer substrate into individual chip forming regions so as to form a plurality of semiconductor devices each having at least one of said thin film passive elements.

15. (Amended) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least one capacitance element.

16. (Amended) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

5 forming a first conductive layer on the circuit element-forming region of said semiconductor substrate;

forming a dielectric material layer on said first conductive layer; and

forming a second conductive layer on said dielectric material layer.

17. (Amended) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

forming on said insulating film one conductive layer having at least two portions; and

forming a dielectric material layer in a clearance between the at least two portions.

18. (Amended) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

forming on said insulating film one conductive layer having at least two portions;

forming said columnar electrodes as plate-like electrodes respectively on the at least two portions; and

forming a dielectric material layer in a clearance between surfaces of said plate-like electrodes.

19. (Amended) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least one inductance element.

20. (Amended) The method of manufacturing a semiconductor device according to claim 19, wherein said forming of each said inductance element comprises:

5 patterning one conductive layer in any one of an angular eddy shape, a rectangular wave shape and a loop shape;

forming said connection pads to include at least one first connection pad that is not electrically connected to any of said columnar electrodes, and at least one second connection pad electrically connected to at least one of said columnar

10 electrodes, and

forming at least two terminals, at least one of which is connected to at least one of said first connection pad and said second connection pad.

21. (Amended) The method of manufacturing a semiconductor device according to claim 20, wherein said forming of the inductance element further comprises forming a magnetic film on said one conductive layer.

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23. (Amended) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least two terminals, at least one of which is electrically connected to one of said columnar electrodes.

24. (Amended) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least two terminals, at least one of which is electrically connected to one of said connection pads.

25. (Amended) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least two terminals, each of which is electrically connected to at least one of said connection pads and said columnar electrodes.

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